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NTE2699
Silicon NPN Transistor
Driver for DC–DC Converter
(Compl to NTE2701)
TO–220 Full Pack Type Package

Features:
- Collector–Emitter Sustaining Voltage: $V_{CE(sus)}$ = 60V Min
- High DC Current Gain: h_{FE} 150 (Min) @ V_{CE} = 2V, I_C = 3A
- Low saturation Voltage: $V_{CE(sat)}$ = 300mV (Max) @ I_C = 8A, I_B = 400mA

Applications:
- Driver for DC/DC Converter
- Actuator Driver

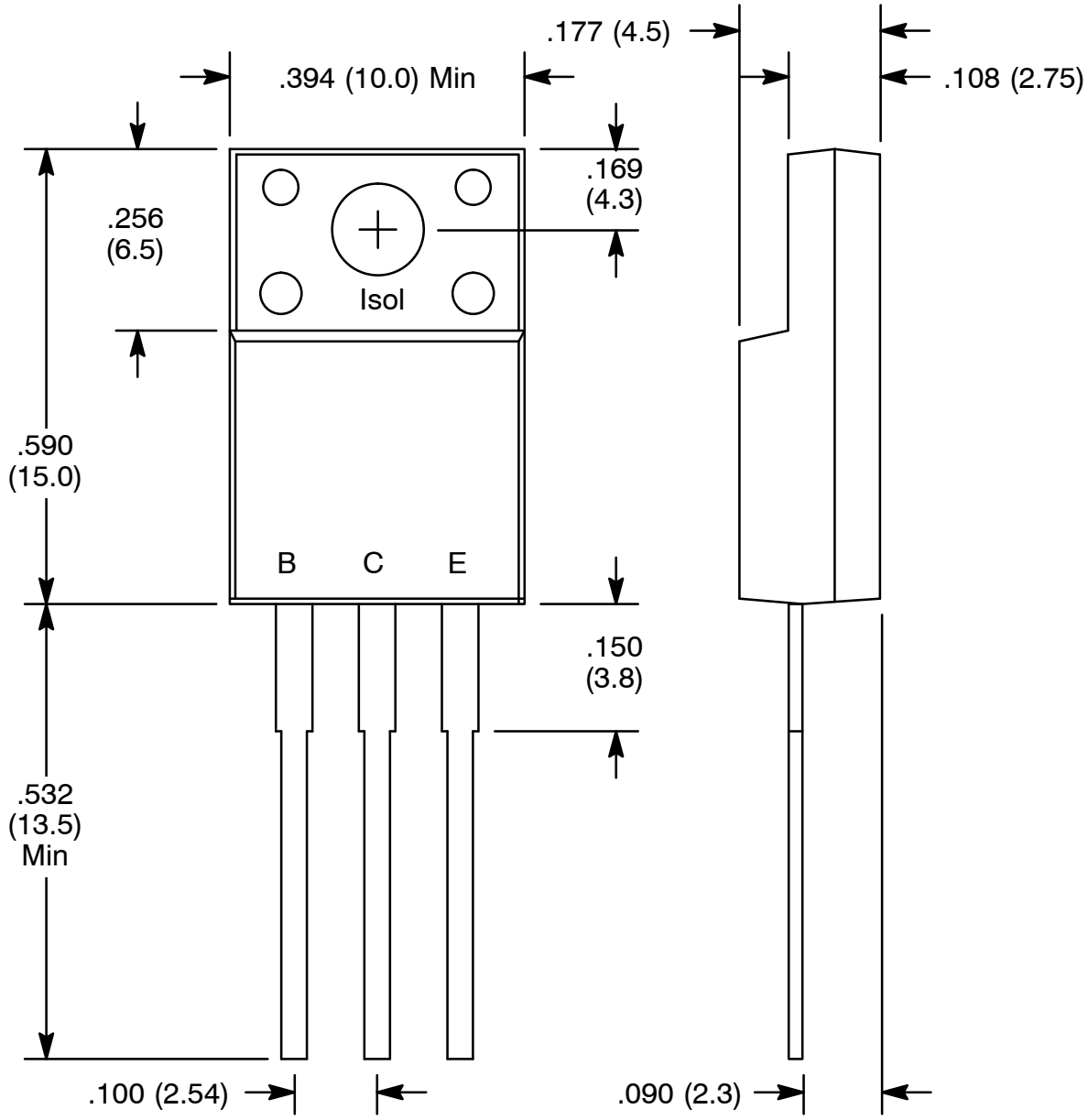
Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 100V
Collector–Emitter Voltage, V_{CEO} 60V
Emitter–Base Voltage, V_{EBO} 7V
Collector Current, I_C
  Continuous 15A
  Pulse 30A
Continuous Base Current, I_B 7.5A
Total Power Dissipation, P_T
  T_C = +25°C 30W
  T_A = +25°C 2.0W
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_C = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Emitter Sustaining Voltage	$V_{CEO(sus)}$	I_C = 50mA, I_B = 0	60	–	–	V
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 8A, I_B = 400mA	–	–	0.3	V
		I_C = 12A, I_B = 600mA	–	–	0.5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 8A, I_B = 400mA	–	–	1.2	V
		I_C = 12A, I_B = 600mA	–	–	1.5	V
Collector Cut–Off Current	I_{CBO}	V_{CB} = 60V, I_E = 0	–	–	10	μA
	I_{CEO}	V_{CE} = 60V, I_B = 0	–	–	1.0	mA
Emitter Cut–Off Current	I_{EBO}	V_{EB} = 5V, I_C = 0	–	–	10	μA
DC Current Gain	h_{FE}	I_C = 3A, V_{CE} = 2V	150	–	300	

RoHS


.177 (4.5)
.394 (10.0) Min
.108 (2.75)
.169
(4.3)
.256
(6.5)
Isol
.590
(15.0)
B
C
E
.150
(3.8)
.532
(13.5)
Min
.100 (2.54)
.090 (2.3)